



# Industrialisation of RF – MEMS Filter technology: Packaging and Outlook

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- **customer request for industrialisation**
- **theory and design**
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- **processes on wafer level**
- **development of packaging design**
- **processes for packaging**
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- **outlook**

# Customers request

**Request:**

**Realisation of a custom specific**

**RF –MEMS Membrane Filter Design**

**Technical specification:**

**down - converter filter at  $K_a$  - band**

**$f_0 = 19.8$  GHz**

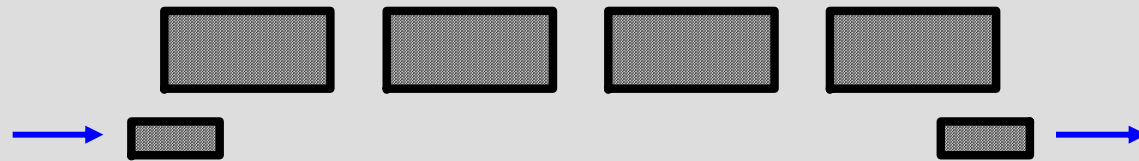
**Initial bandwidth  $\sim 0.75$  GHz**

**min. loss at  $f_0 \sim -3$  dB**

**etc.**

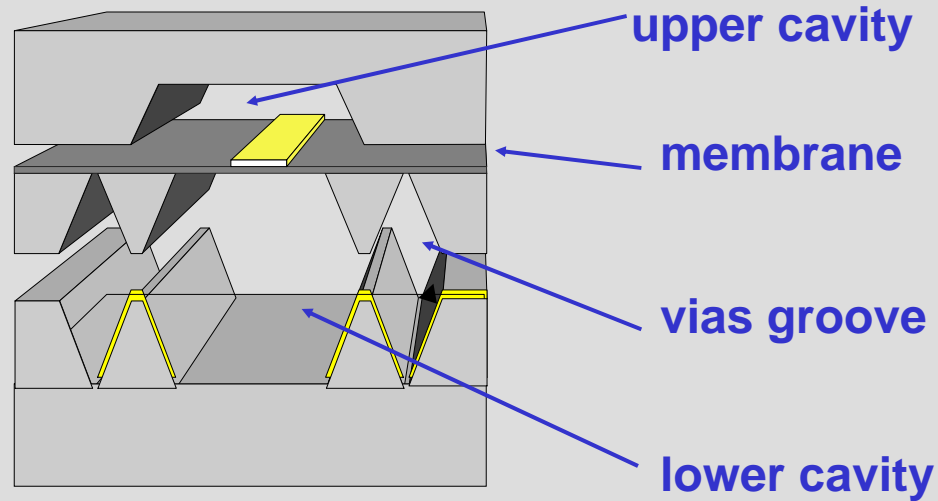
# Theory and Design

Please remember on the pervious talk by Dr. Chatras

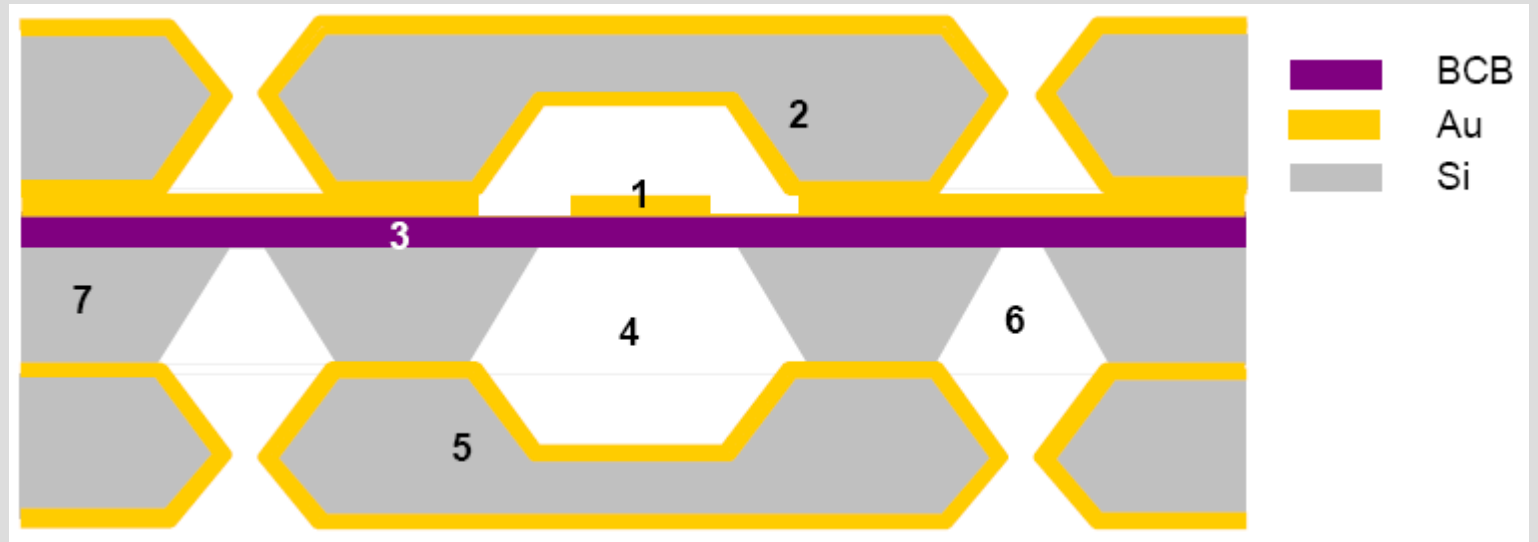


# Device overview I

The devices are built up out of 3 stacked wafers forming a resonating cavity:

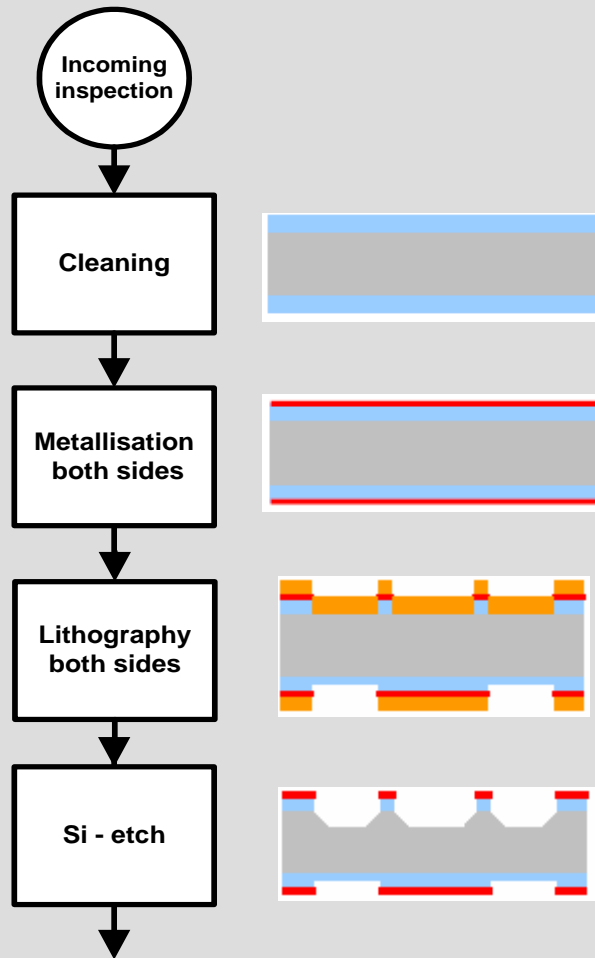


## Device overview II



1. *microstrip Line (waveguiding part)*
2. *ground metallisation top wafer*
3. BCB membrane
4. cavity divided by BCB membrane
5. *ground metallisation bottom wafer*
6. electromagnetic shielding
7. high ohmic Si

# Wafer Processes I

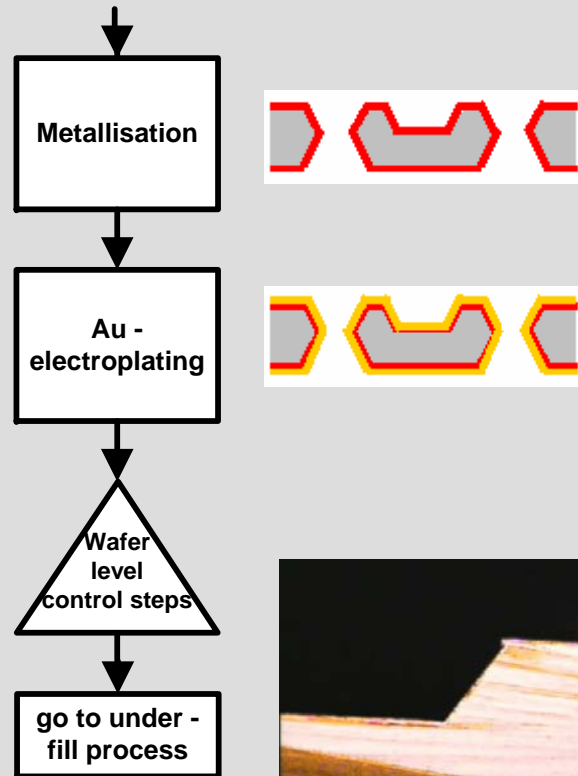


## Process follow up for Bottom wafer (I):

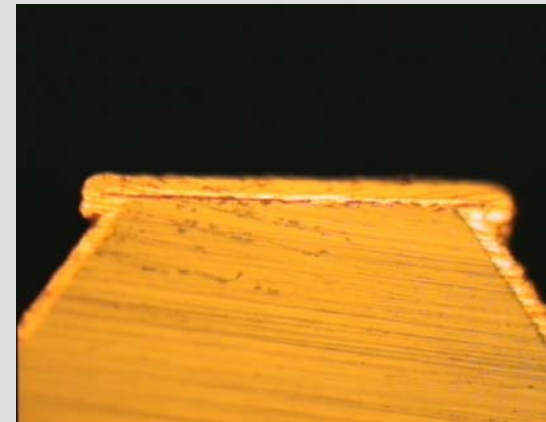
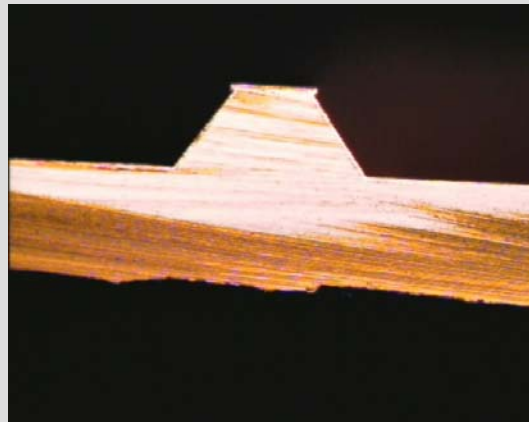
- cleaning
- metallisation (both sides)
- lithography (both sides)
- Si - etch

# Wafer Processes II

**Process follow up for Bottom wafer (II):**

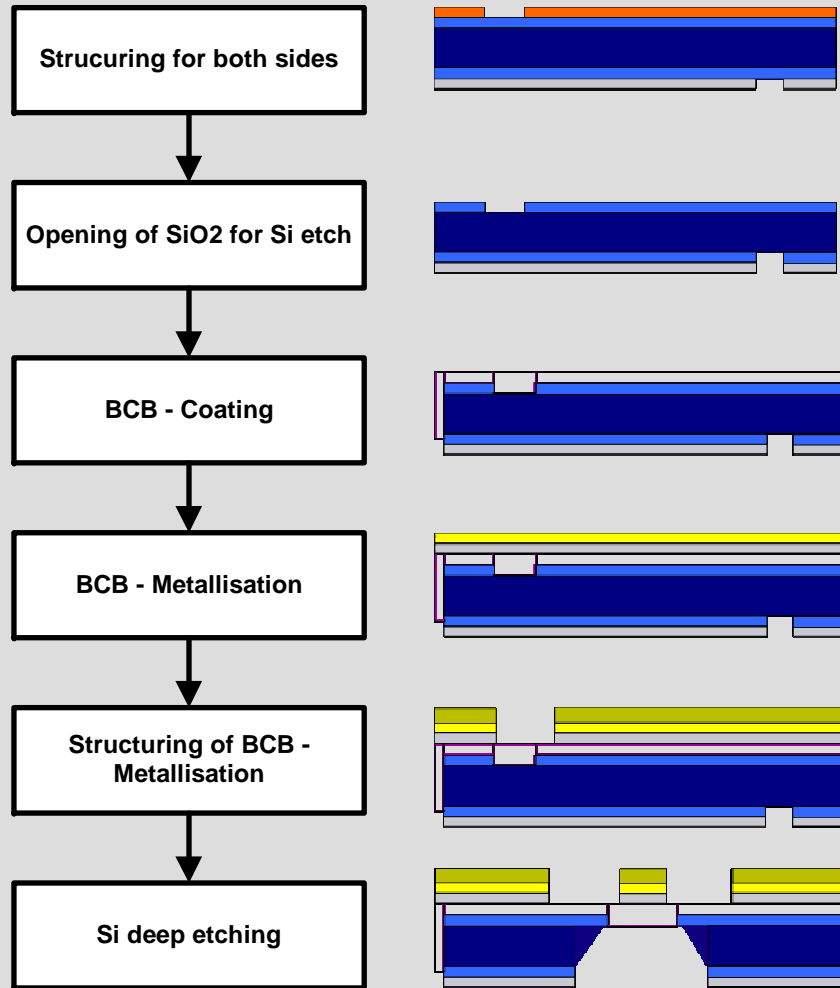


- 2nd metallisation
- electroplating (top 8.5; slope 7, bottom 6.7  $\mu\text{m Au}$ )





# Wafer Processes III

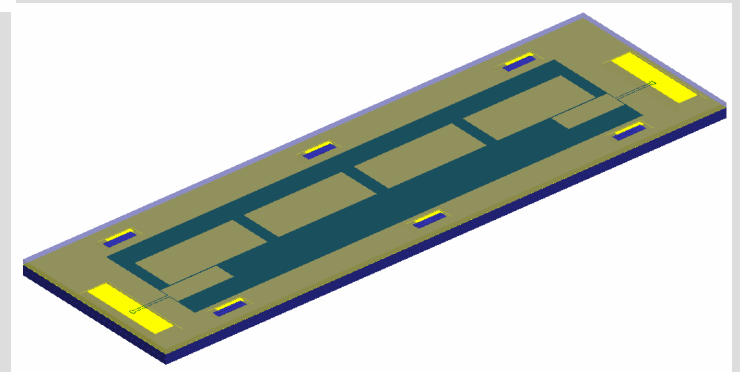
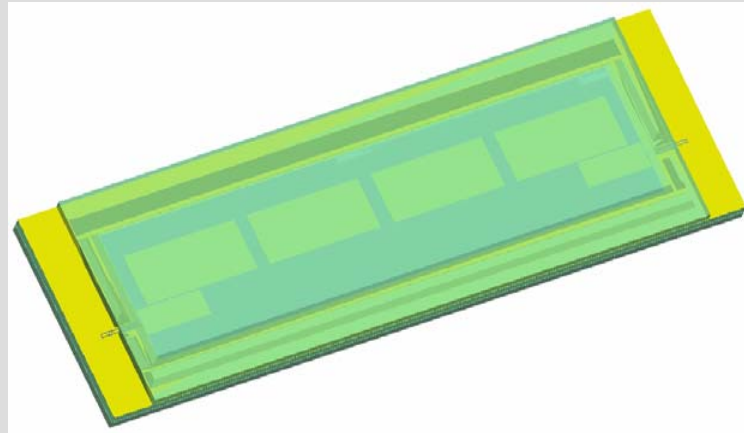


**Middle wafer key processes:**

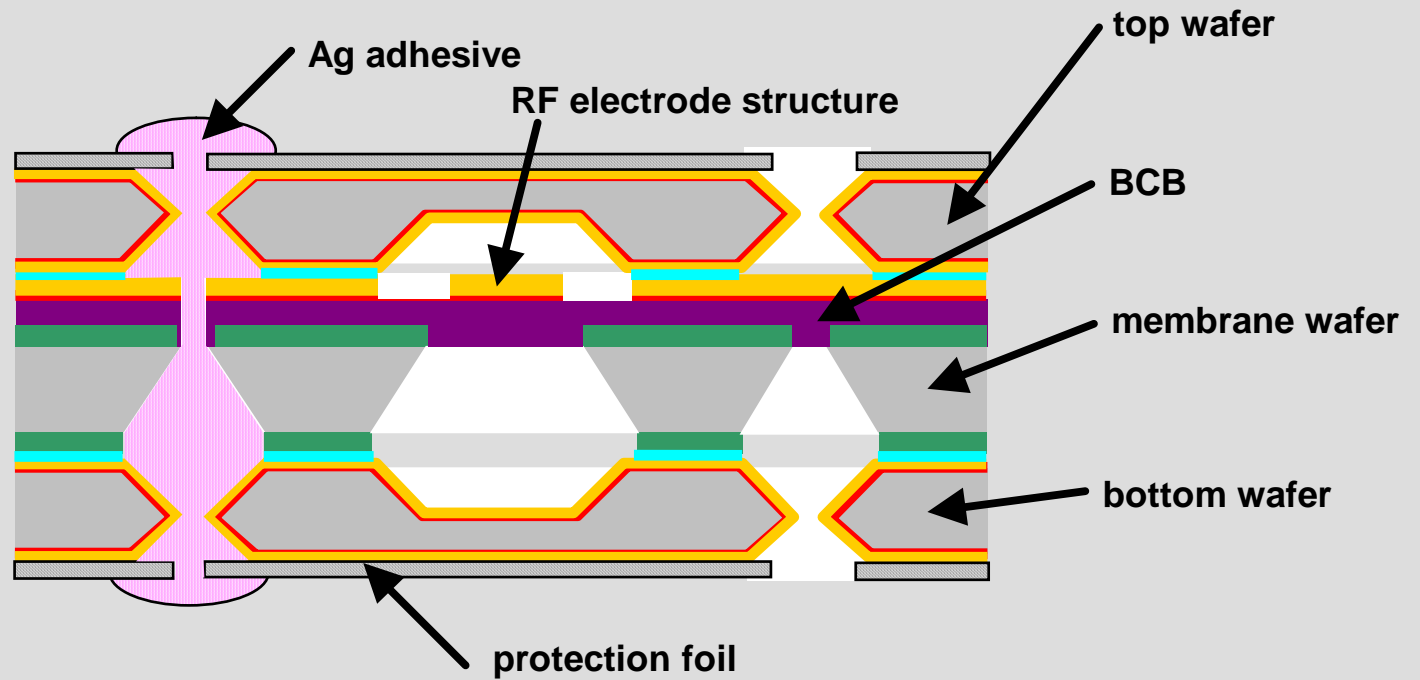
- BCB – Processing
- Si – etch simultaneously
- handling of thinned wafers

# Development of the Packaging Design I

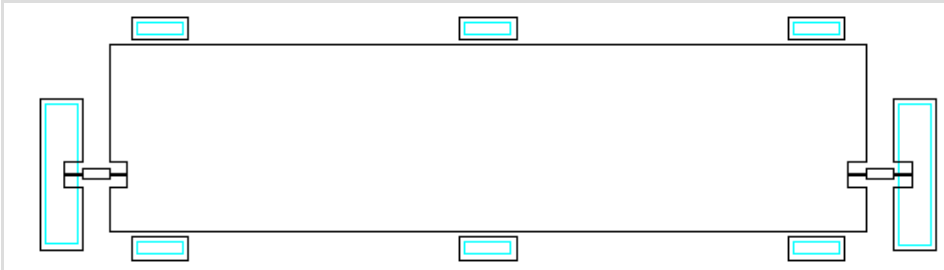
**The design of packaging was improved step by step:**



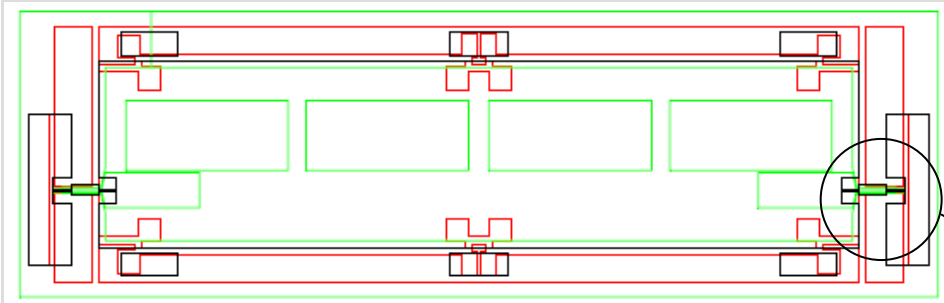
# Development of the Packaging Design II



# Development of the Packaging Design III

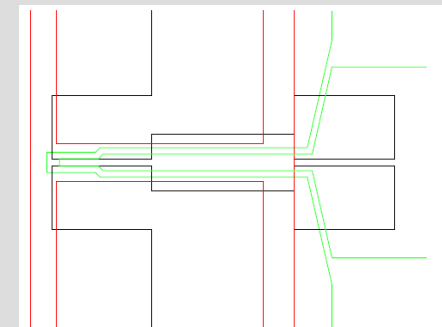


**Mask change  
top wafer**

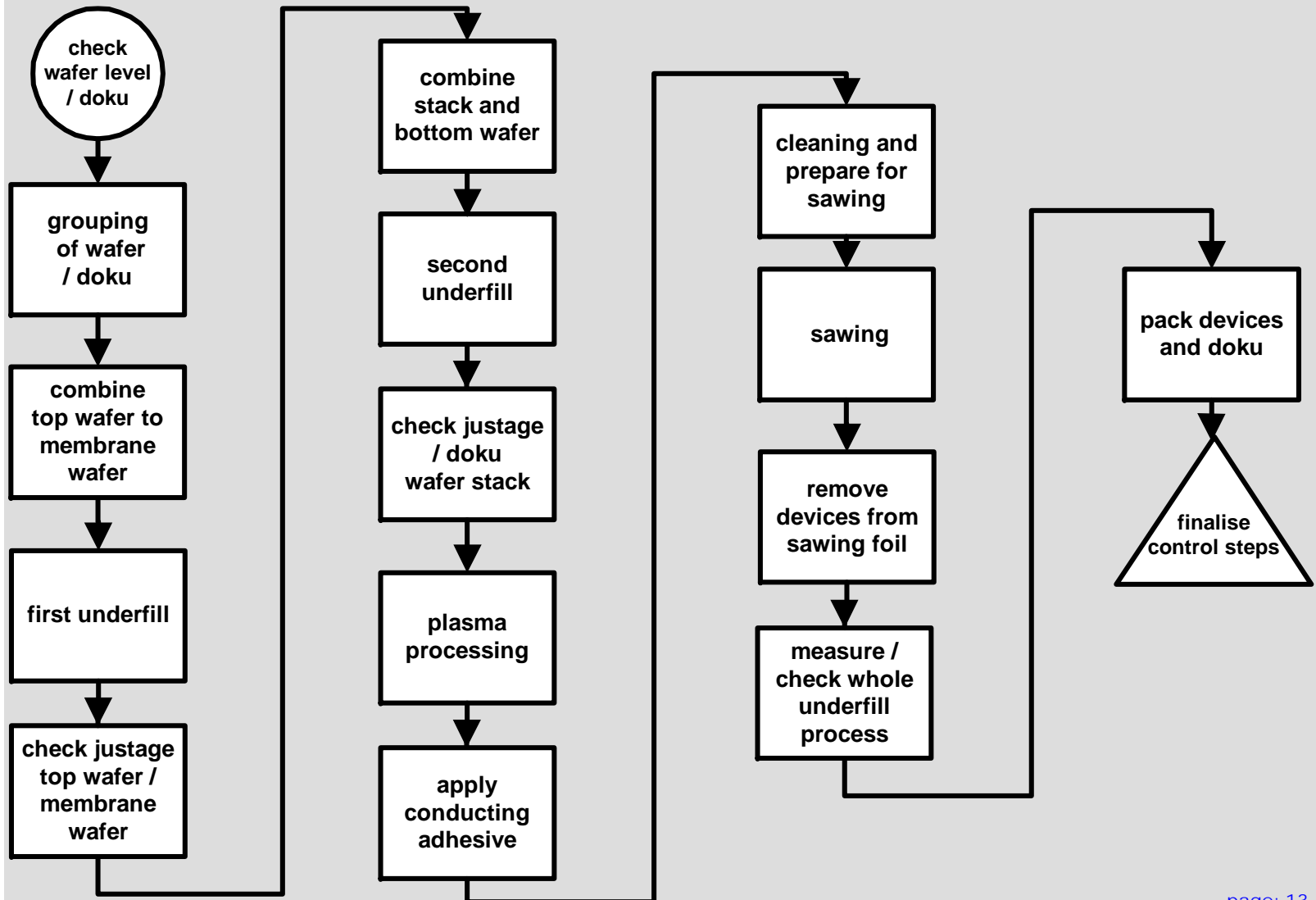


**Mask change  
middle wafer**

**input / output - coupling**

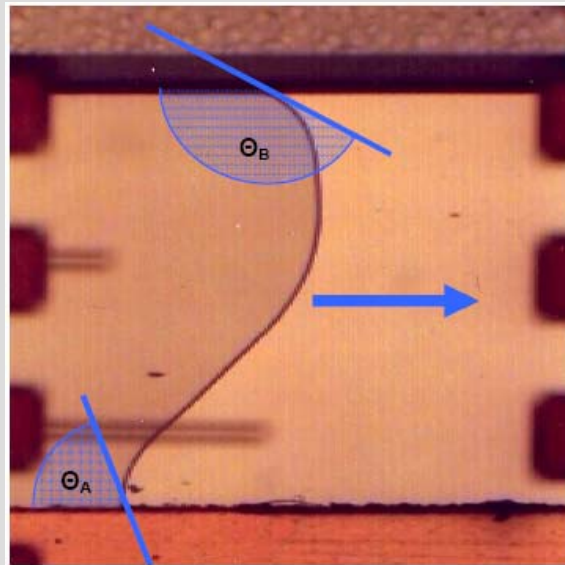


# Processes Packaging I



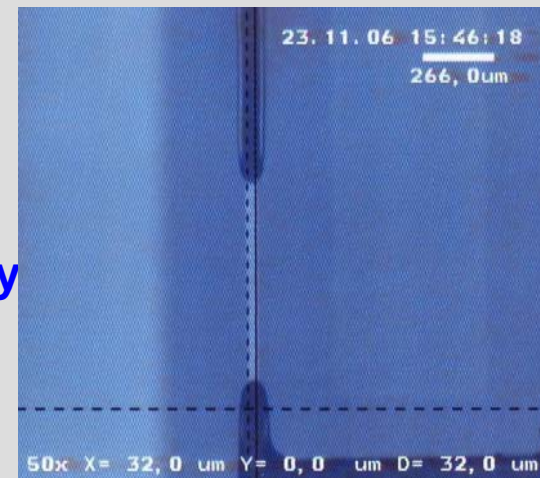
# Processes Packaging II

## Underfill Process:



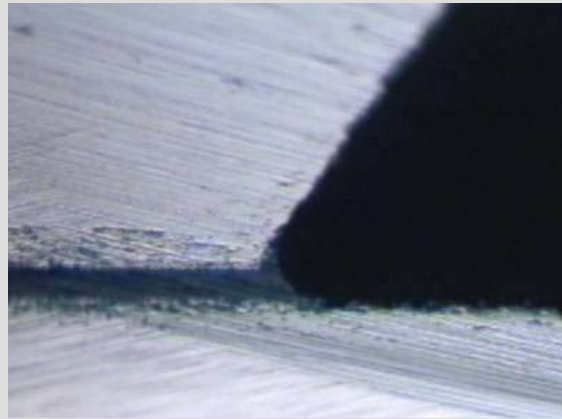
The move of the expansion line of underfill (50°C) between Si and glass

The expansion line's velocity reduces at narrow lines.

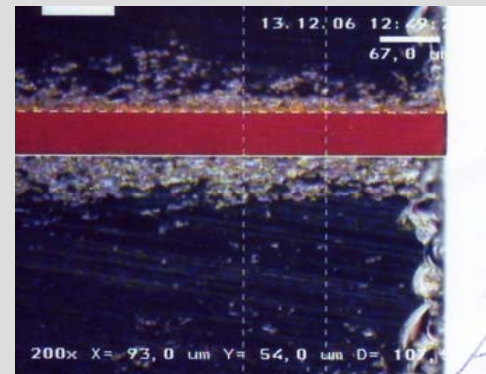
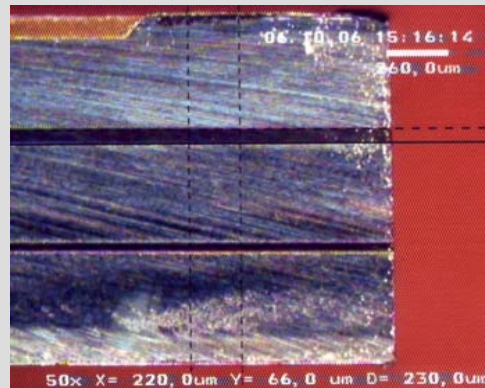


# Processes Packaging III

## Complete Underfill Process:



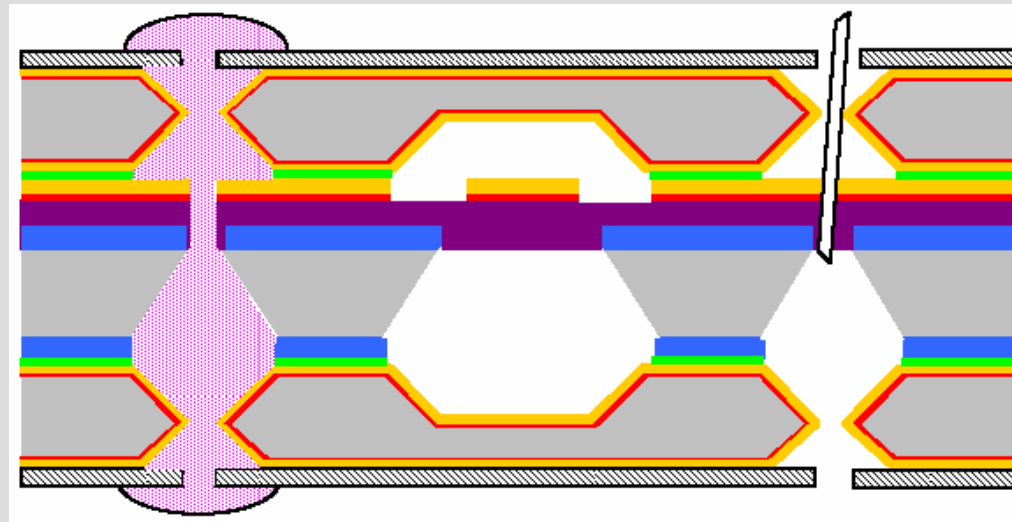
by selecting proper process parameters a well defined flow of underfill can be achieved



complete / non - complete fill of device edges

# Processes Packaging IV

## conducting adhesive glue process (I):

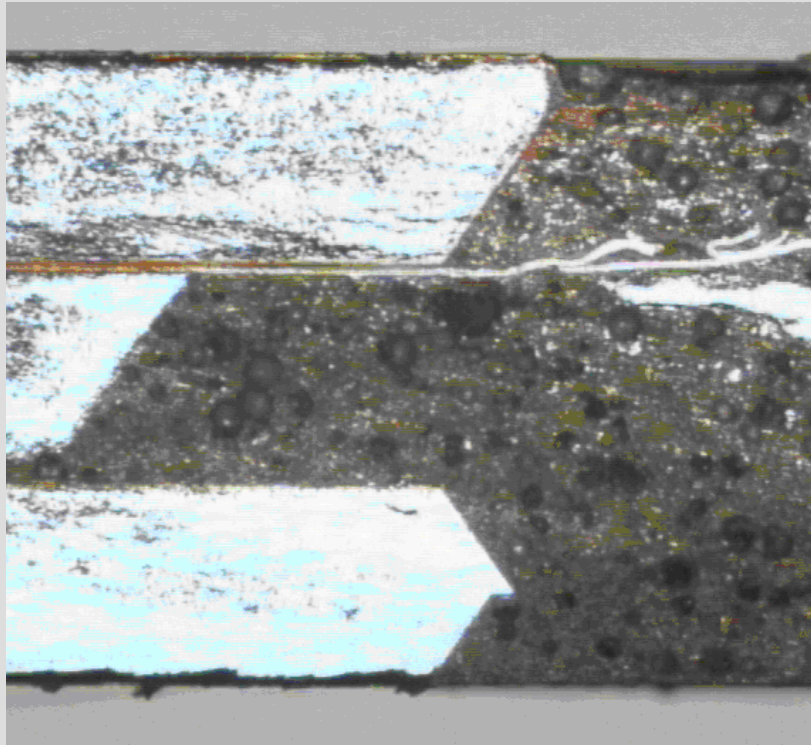


	Cr		Underfill
	Au		conducting adhesive
	SiO <sub>2</sub>		BCB
	Si		Kapton foil



# Processes Packaging V

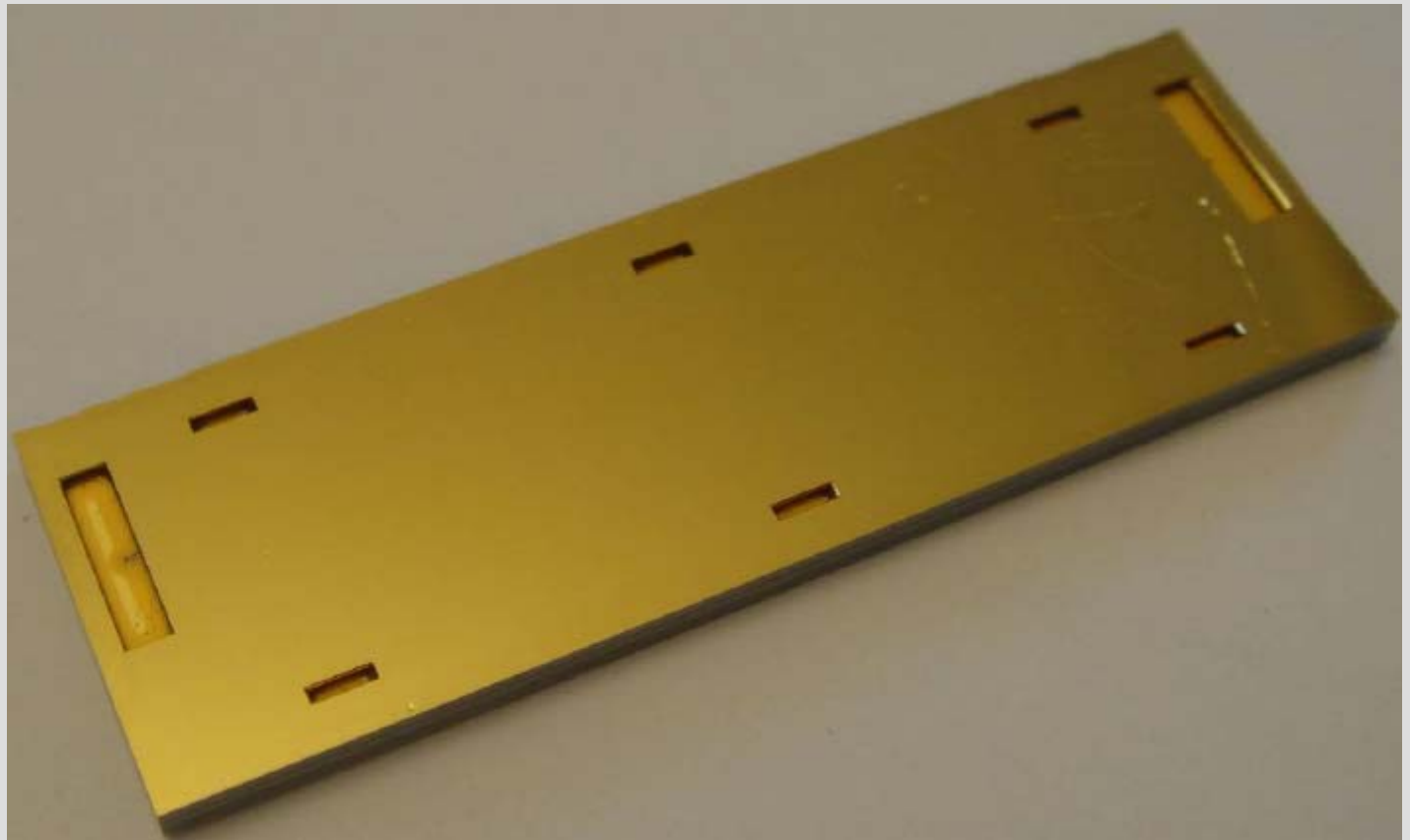
## conducting adhesive glue process (II):



**by selecting proper process parameters a well defined flow of conducting adhesive can be achieved**

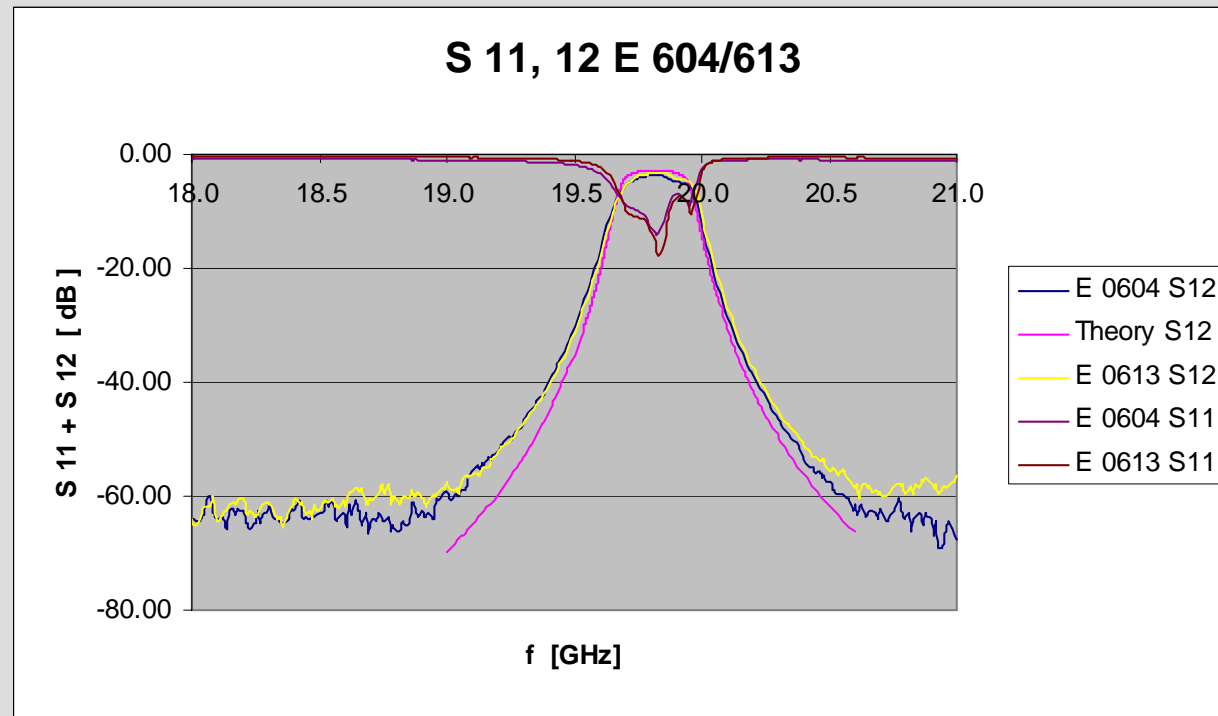
# realised filter

- picture



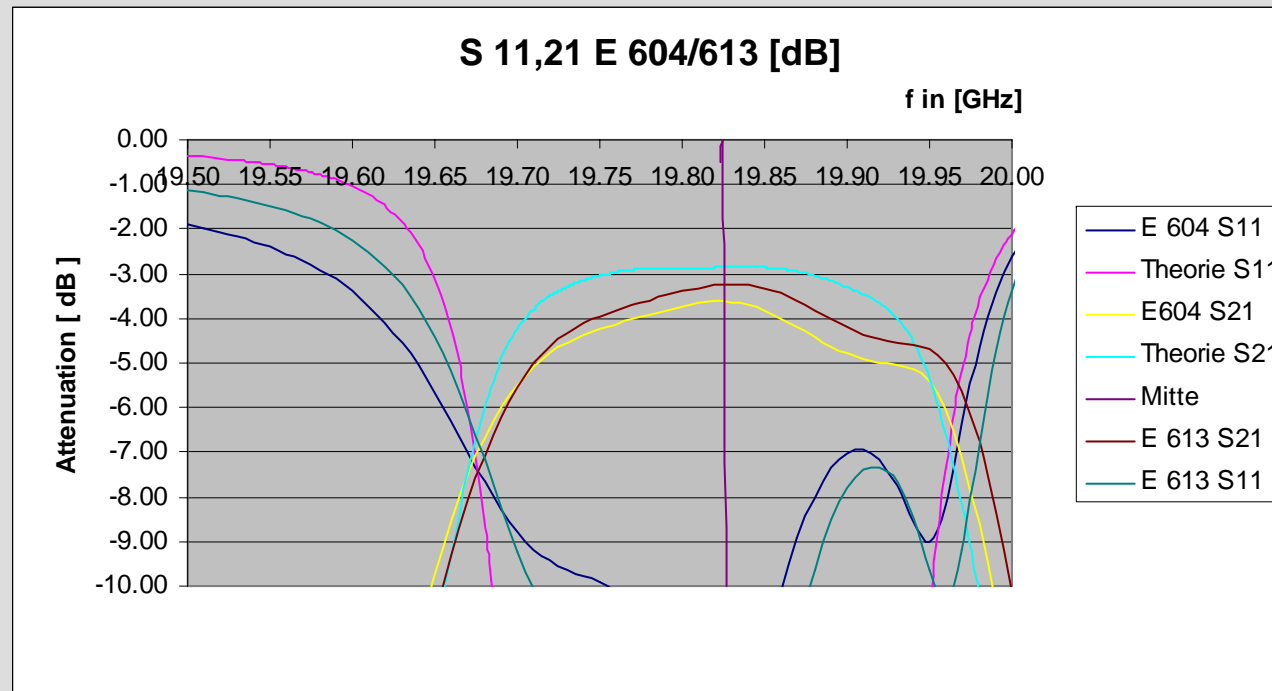
# realised filter

## - RF – Measurements I (overview)



# realised filter

## - RF – Measurements II (detail)



# Outlook I

**A new project is launched with ESA to qualify processes for space applications and to name RMT on the preferred supplier list.**

**RMT is enlarging its offer to leading system houses as an industrial supplier to use its facilities for improved RF – designs.**

# Outlook II

**RMT is open to realise new customer specific designs.**

**All these designs are developed with the customer and remain customers property.**